

Amendments to the Specification

Please replace paragraph [0001] with the following amended version of that paragraph:

This application is related to US Patent Application No. 10/789,103 [~~Attorney Docket NOVL P094~~], filed on February 17, 2004, naming Wu et al. as inventors and titled "METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS," which claims priority from US Provisional Patent Application No. 60/524,330, filed on November 20, 2003, naming Wu et al. as inventors and title "METHODS FOR PRODUCING LOW-K CDO FILM OF LOW RESIDUE STRESS WITH DIELECTRIC CONSTANT <3.0," both of which are incorporated herein by reference for all purposes.

Please replace paragraph [0042] of the specification with the following amended version of that paragraph:

Various deposition techniques may be employed to form the CDO dielectric materials of this invention. These include various other forms of chemical vapor deposition (CVD) including plasma enhanced CVD (PECVD) and high-density plasma CVD (HDP CVD). HDP CVD of dielectric materials is described in various sources including commonly assigned US Patent Application No. 09/996,619, filed November 28, 2001 by Atiye Bayman et al. and titled "Gap Fill for High Aspect Ratio Structures", which is incorporated herein by reference for all purposes. Additionally, other techniques such as spin on techniques and deposition from supercritical solutions may be employed. But for many applications of this invention, a plasma based CVD process is employed.